

Abstracts

A Microwave Model for the Dual-Gate GaAs MESFET

G.S.F. Mau. "A Microwave Model for the Dual-Gate GaAs MESFET." 1981 MTT-S International Microwave Symposium Digest 81.1 (1981 [MWSYM]): 43-45.

A simplified dual-gate GaAs FET microwave model consisting of a cascode connection of single-gate FET's is developed, tested for validity, and discussed herein. Computer generated S-parameters of the model are compared to those measured for an actual device in the 2 to 9 GHz frequency range.

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